

64. (New) The method as in Claim 63, wherein creating the first halo region further comprises a second providing of the first mask to the thyristor portion of each T-RAM cell, the first mask again covering the second portion of the thyristor portion and leaving the first portion of the thyristor portion unmasked, and providing an implant of the second polarity type to the first portion of the thyristor portion of each T-RAM cell, the first halo region being formed upon application of the implant of the second polarity type.

65. (New) The method as in Claim 58, wherein the first mask further leaves a transfer gate portion of each of the plurality of T-RAM cells unmasked, the halo implant of the first polarity type also being provided to the entire transfer gate portion of each of the plurality of T-RAM cells.

#### REMARKS

This amendment is submitted in response to the Office Action dated December 6, 2001. Claims 1-42 have been cancelled above without prejudice and new Claims 43-65 have been inserted. Since new Claims 43-65 are now pending in the application, it is submitted that the prior election/restriction requirement given for Claims 1-42 in paragraphs 2-7 of the Office Action is no longer applicable. It is further submitted that an election/restriction requirement is not applicable for current Claims 43-65 under the standard given in paragraph 3 of the Office Action.

In response to the drawing objection in paragraphs 8 and 9 of the Office Action, a proposed correction to Fig. 13 is submitted herewith. A revised formal drawing will be sent after approval of the correction and allowance of the application by the Examiner.

In paragraphs 12 and 13 of the Office Action, now cancelled Claims 1-13 were rejected under 35 U.S.C. 103(a) as being unpatentable of U.S. Patent No. 6,229,161 to Nemati et al. in view of U.S. Patent No. 5,945,715 to Kuriyama.

New independent Claim 43 recites "A memory system comprising a plurality of T-RAM cells arranged in an array, each of the plurality of T-RAM cells comprising a thyristor portion having two halo regions having different polarities". Independent Claim 56 has analogous recitations. Among other things, two halo implant regions having

different polarities provide advantages including reduction of the size of the thyristor and T-RAM cell, as well as improved control by the gate of the thyristor.

Nemati is directed to a T-RAM cell having a transfer gate and a PNP thyristor device. Nemati fails to disclose or suggest at least the Claim 43 recitation of the T-RAM cells comprising "a thyristor portion having two halo regions having different polarities". Thus, Claim 43, and by analogous reasoning, independent Claim 56, are patentably distinct from Nemati for at least this reason. In addition, neither the Kuriyama or any other of the references cited in the Office Action disclose this aspect of Claims 43 and 56. Thus, they are also patentably distinct from these references for at least this reason.

Without conceding the patentability per se of dependent Claims 44-55 and 57-65, it is submitted that they are also patentably distinct from the above-cited art by virtue of their dependency on independent Claims 43 and 56. Thus, early and favorable allowance of all of the claims pending in the application, namely, Claims 43-65, is respectfully requested.

Should the Examiner believe that a telephone call or a personal interview may help facilitate resolution of any remaining matters, it is requested that the Examiner contact Applicants' attorney at the number given below.

Respectfully submitted,



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